

## MPSA194

### PNP SILICON TRANSISTOR

# PNP EPITAXIAL SILICON TRANSISTOR

#### DESCRIPTION

The UTC **MPSA194** is designed for high voltage low power switching applications especially for use in telephone and telecommunication circuits.

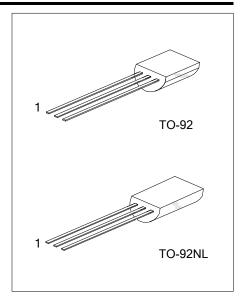
#### FEATURES

- \* Collector-Emitter Voltage: V<sub>CEO</sub>=400V
- \* Power Dissipation: 1.0W

#### APPLICATIONS

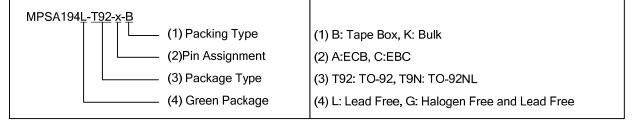
- \* Telephone Circuit
- \* Telecommunication Circuit

#### ORDERING INFORMATION

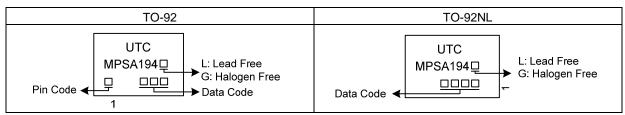


Ordering Number		Deelvere	Pin Assignment			Deelvine	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MPSA194L-T92-C-B	MPSA194G-T92-C-B	TO-92	Е	В	С	Tape Box	
MPSA194L-T92-C-K	MPSA194G-T92-C-K	TO-92	Е	В	С	Bulk	
MPSA194L-T92-A-B	MPSA194G-T92-A-B	TO-92	Е	С	В	Tape Box	
MPSA194L-T92-A-K	MPSA194G-T92-A-K	TO-92	Е	С	В	Bulk	
MPSA194L-T9N-B	MPSA194G-T9N-B	TO-92NL	Е	С	В	Tape Box	
MPSA194L-T9N-K	MPSA194G-T9N-K	TO-92NL	Е	С	В	Bulk	
Note: Pin assignment: B: Base	C: Collector E: Emitter						

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#### MARKING INFORMATION



#### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector to Base Voltage	V <sub>CBO</sub>	-400	V	
Collector to Emitter Voltage	V <sub>CEO</sub>	-400	V	
Emitter to Base Voltage	V <sub>EBO</sub>	-6	V	
Collector Current	lc	-800	mA	
Collector Dissipation (T <sub>A</sub> =25°C)	Pc	1.0	W	
Junction Temperature	TJ	150	°C	
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

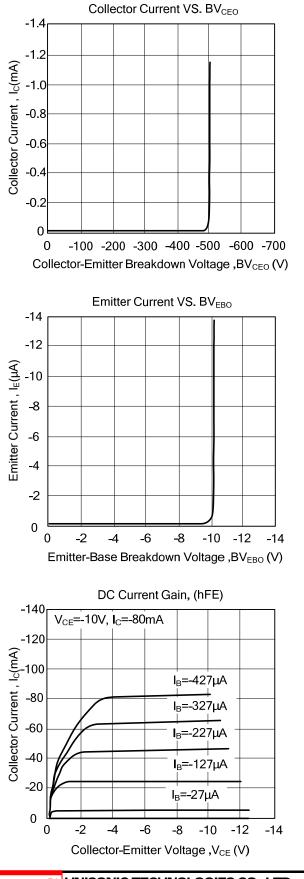
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_{CBO}$	I <sub>C</sub> =-100μA, I <sub>E</sub> =0A	-400			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	I <sub>C</sub> =-1mA, I <sub>B</sub> =0A	-400			V
Collect Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-400 V, I <sub>E</sub> =0A			-10	μA
Collect Cut-off Current	I <sub>CEO</sub>	V <sub>CB</sub> =-200 V, V <sub>BE</sub> =0V			-1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB} = -6 V, I_{C} = 0A$			-0.2	μA
		V <sub>CE</sub> =-10 V ,I <sub>C</sub> =-1mA	50			
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =-10 V ,I <sub>C</sub> =-20mA	50		800	
		V <sub>CE</sub> =-10 V ,I <sub>C</sub> =-80mA	40			
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	I <sub>C</sub> =-20mA, I <sub>B</sub> =- 2mA			-0.9	V
	V	I <sub>C</sub> =-20mA, I <sub>B</sub> =- 4mA			-0.2	V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	Ι <sub>C</sub> =-80mA, Ι <sub>B</sub> =- 2mA			-1.2	V
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> =-20 V, I <sub>E</sub> =0A, f =1MHz			30	pF
Current Gain Bandwidth Product	f <sub>T</sub>	$V_{CE}$ =-20V, $I_{E}$ =-10A, f =1MHz	10			$MH_Z$

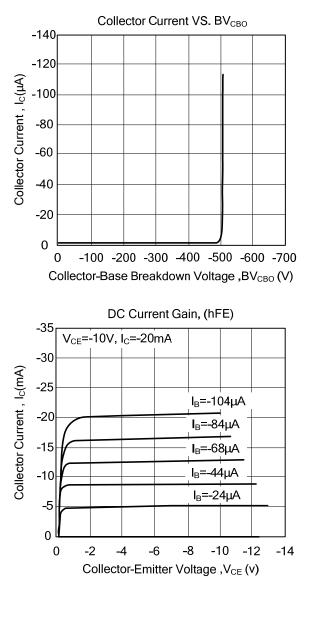


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#### TYPICAL CHARACTERISTICS





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